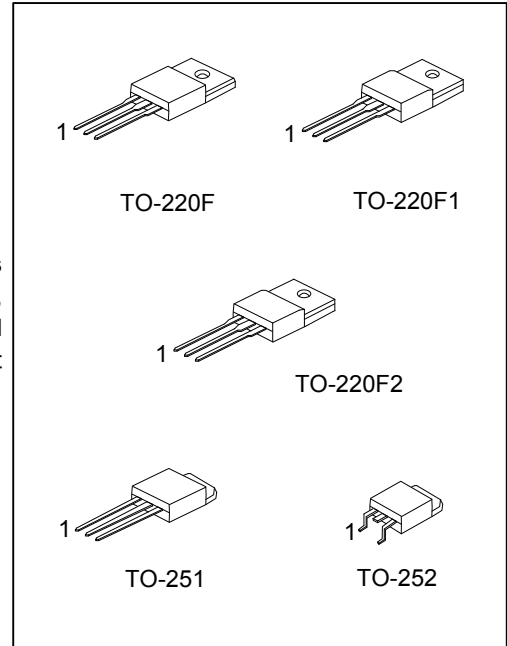
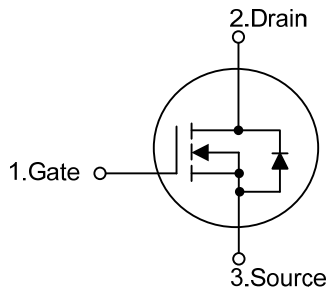


**6NM50****Power MOSFET****6A, 500V N-CHANNEL
SUPER-JUNCTION MOSFET****DESCRIPTION**

The UTC 6NM50 is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at AC-DC converters for power applications.

FEATURES

- * $R_{DS(on)} \leq 0.9 \Omega$ @ $V_{GS}=10V$, $I_D=3.0A$
- * Improved dv/dt capability
- * Fast switching
- * 100% avalanche tested

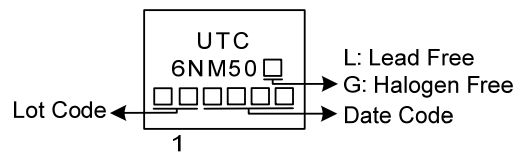
SYMBOL**ORDERING INFORMATION**

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
6NM50L-TF1-T	6NM50G-TF1-T	TO-220F1	G	D	S	Tube
6NM50L-TF2-T	6NM50G-TF2-T	TO-220F2	G	D	S	Tube
6NM50L-TF3-T	6NM50G-TF3-T	TO-220F	G	D	S	Tube
6NM50L-TM3-T	6NM50G-TM3-T	TO-251	G	D	S	Tube
6NM50L-TN3-R	6NM50G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

	(1) Packing Type
	(2) Package Type
	(3) Green Package
(1) T: Tube, R: Tape Reel	
(2) TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2	
TM3: TO-251, TN3: TO-252	
(3) G: Halogen Free and Lead Free, L: Lead Free	

■ MARKING



■ **ABSOLUTE MAXIMUM RATINGS** ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	500	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current ($T_C=25^\circ\text{C}$)	Continuous	I_D	6.0	A
	Pulsed (Note 2)	I_{DM}	24	A
Avalanche Current (Note 2)		I_{AR}	2.6	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	155	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.4	V/ns
Power Dissipation	TO-220F/TO-220F1	P_D	20	W
	TO-220F2			
	TO-251/TO-252		21	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L=46\text{mH}$, $I_{AS}=2.6\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD}\leq 6.0\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ **THERMAL DATA**

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220F/TO-220F1	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-220F2			
	TO-251/TO-252		110	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220F/TO-220F1	θ_{JC}	6.25	$^\circ\text{C}/\text{W}$
	TO-220F2			
	TO-251/TO-252		5.95 (Note)	$^\circ\text{C}/\text{W}$

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

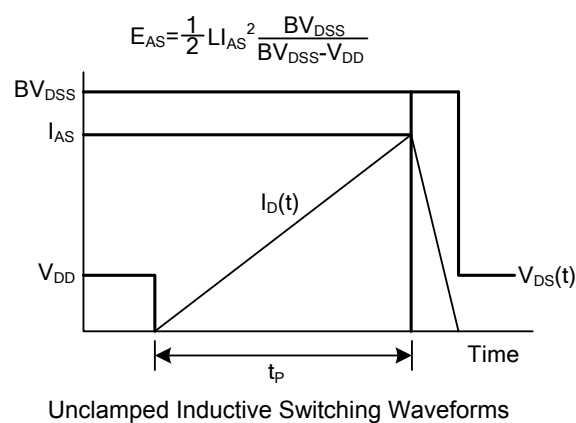
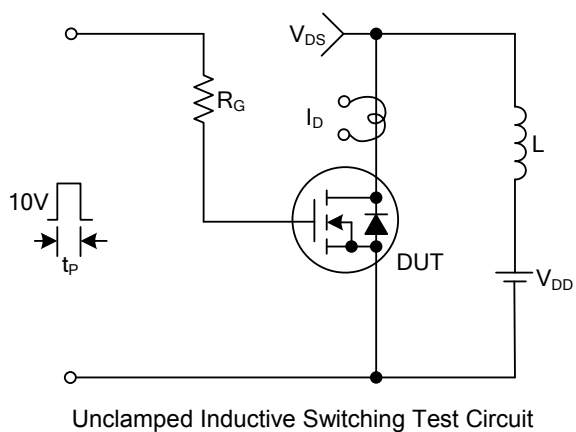
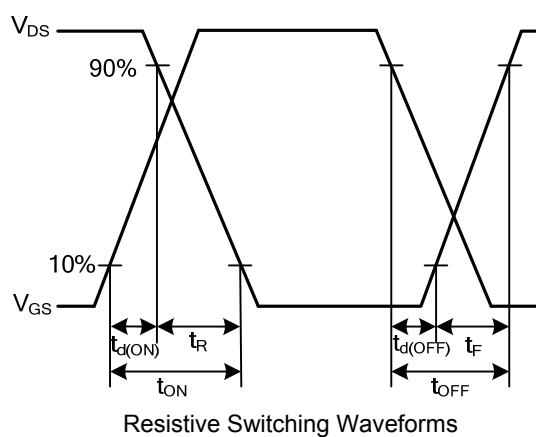
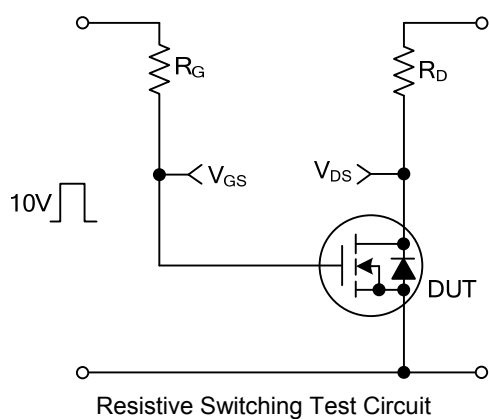
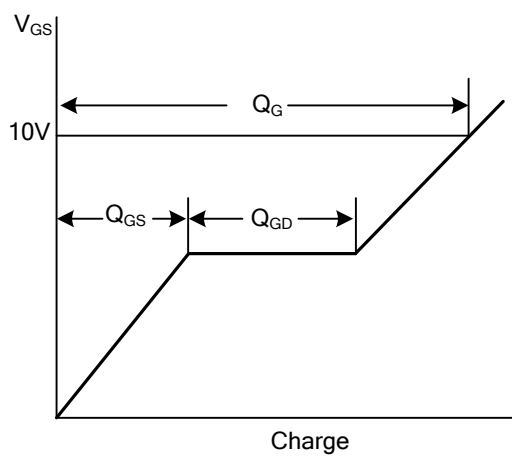
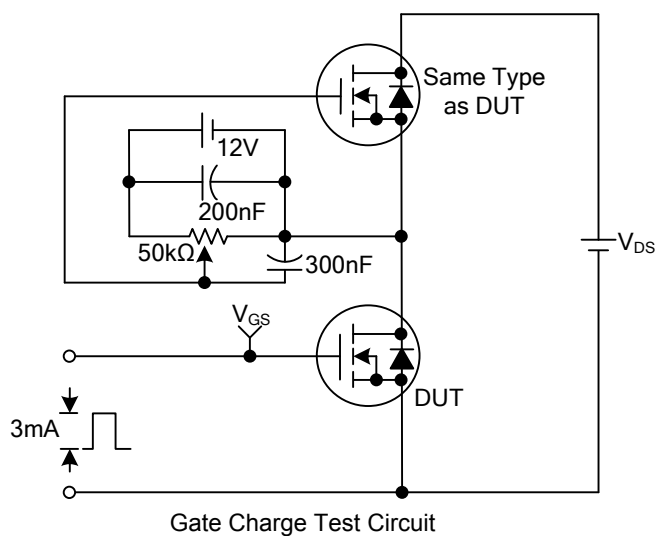
■ **ELECTRICAL CHARACTERISTICS** ($T_J = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} =0V, I _D =250μA	500			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =500V, V _{GS} =0V			10	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} =30V, V _{DS} =0V			100	nA
	Reverse		V _{GS} =-30V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.5		4.5	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =3.0A			0.9	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1.0MHz		295		pF
Output Capacitance		C _{OSS}			200		pF
Reverse Transfer Capacitance		C _{RSS}			40		pF
SWITCHING CHARACTERISTICS							
Total Gate Charge (Note 1)		Q _G	V _{DS} =50V, V _{GS} =10V, I _D =1.3A , I _G =100μA (Note 1, 2)		37		nC
Gate to Source Charge		Q _{GS}			3		nC
Gate to Drain Charge		Q _{GD}			10		nC
Turn-ON Delay Time (Note 1)		t _{D(ON)}	V _{DD} =30V, V _{GS} =10V, I _D =0.5A, R _G =25Ω (Note 1, 2)		35		nS
Rise Time		t _R			68		nS
Turn-OFF Delay Time		t _{D(OFF)}			130		nS
Fall-Time		t _F			70		nS
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I _S				6	A
Maximum Body-Diode Pulsed Current		I _{SM}				24	A
Drain-Source Diode Forward Voltage (Note 1)		V _{SD}	V _{GS} =0V, I _S =6.0A			1.4	V
Body Diode Reverse Recovery Time (Note 1)		t _{rr}	V _{GS} =0V, I _S =6.0A,		285		nS
Body Diode Reverse Recovery Charge		Q _{rr}	dl _F /dt=100A/μs(Note1)		2.3		μC

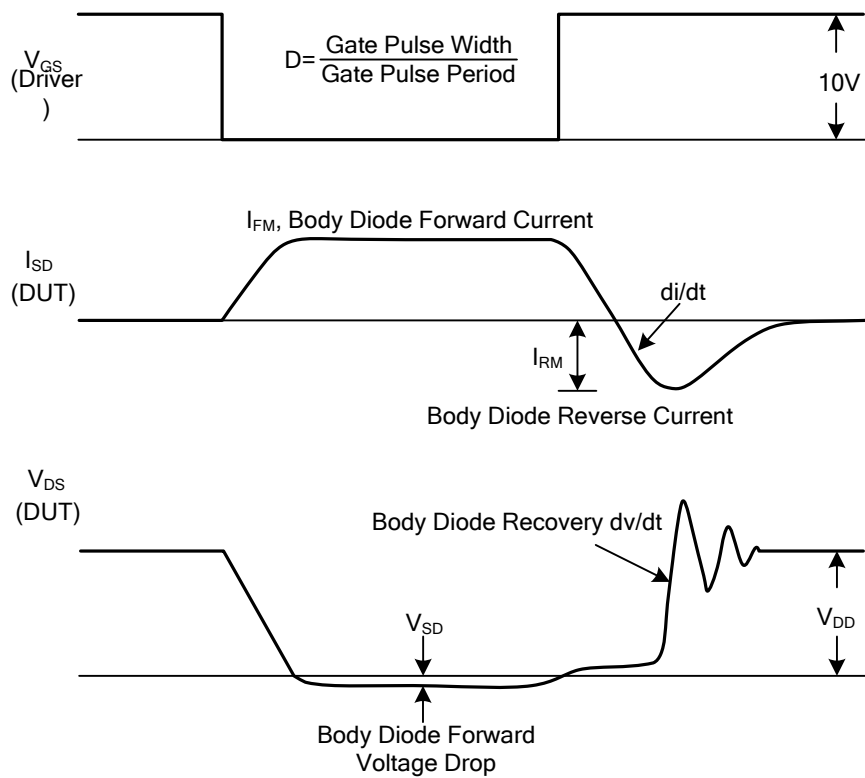
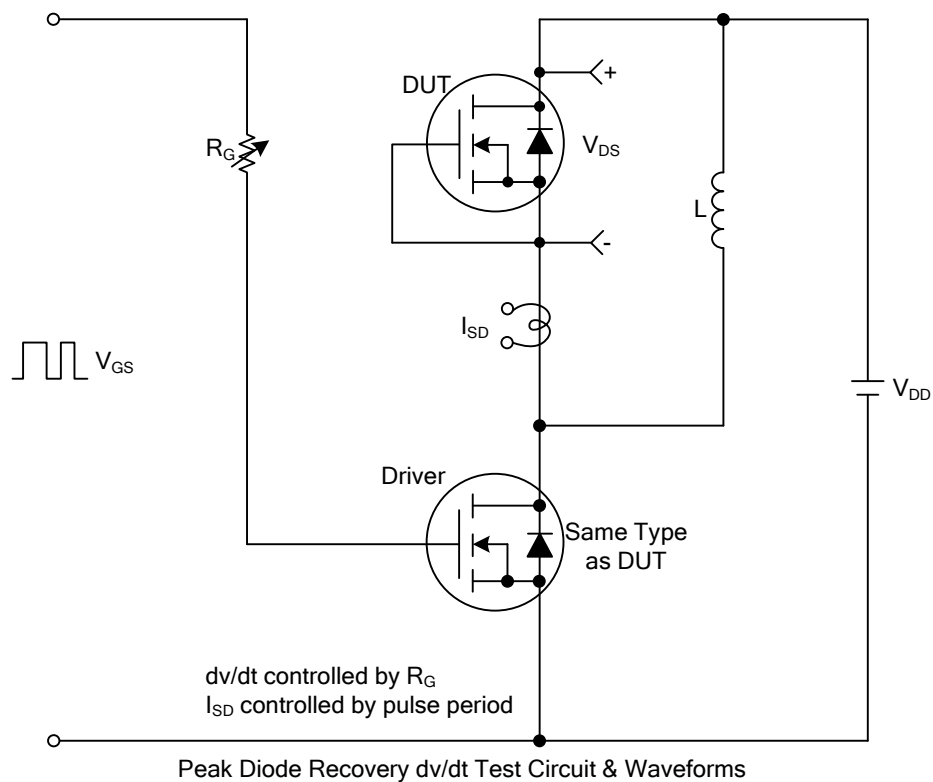
Notes: 1. Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating ambient temperature.

■ TEST CIRCUITS AND WAVEFORMS



■ TEST CIRCUITS AND WAVEFORMS(Cont.)



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